

**IN THE CLAIMS:**

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered). Please CANCEL claims 1-6 without prejudice or disclaimer; AMEND claim 7 and ADD new claims 23 and 24 in accordance with the following:

1 - 6 (cancelled)

7. (currently amended) A method of manufacturing a flat panel display, comprising:

forming a pixel electrode and a semiconductor layer, spaced apart from each other, on a substrate;

forming a first insulating layer over a surface of the substrate to cover the pixel electrode and the semiconductor layer ~~after the forming a pixel electrode and a semiconductor layer;~~

forming a gate electrode on a portion of the first insulating layer corresponding to a location of the semiconductor layer;

forming a second insulating layer over the surface of the substrate to cover the gate electrode;

forming contact holes in the first and second insulating layers to expose a portion of the pixel electrode and portions of the semiconductor layer;

forming source and drain electrodes on the second insulating layer electrically connecting the source electrode to the semiconductor layer through one of the contact holes, and electrically connecting the drain electrodes to the semiconductor layer and the pixel electrode through another one of the contact holes;

forming a photoresist layer over the surface of the substrate exposing a portion of the second insulating layer over the pixel electrode; and

forming an opening portion by etching the first and second insulating layers to expose a portion of the pixel electrode, using the photoresist layer as a mask;

forming an electroluminescence (EL) layer on the exposed portion of the pixel electrode;  
and

forming a cathode over the EL layer and the photoresist layer.

8.       **(original)** The method of claim 7, wherein said forming of the pixel electrode and the semiconductor layer comprises forming the pixel electrode after forming the semiconductor layer.

9.       **(original)** The method of claim 7, wherein said forming of the pixel electrode and the semiconductor layer comprises forming the pixel electrode before forming the semiconductor layer.

10.      **(cancelled)**

11.      **(original)** The method of claim 7, wherein said forming of the semiconductor layer comprises:

depositing an amorphous silicon layer on the substrate;  
annealing the amorphous silicon layer to form a polysilicon layer; and  
patterning the polysilicon layer to form the semiconductor layer.

12.      **(original)** The method of claim 7, wherein said forming of the semiconductor layer further comprises:

forming a polysilicon layer on the substrate; and  
patterning the polysilicon layer to form the semiconductor layer.

13.      **(original)** The method of claim 12, wherein said forming of the gate electrode comprises:

depositing a first metal layer on the first insulating layer; and  
patterning the first metal layer to form the gate electrode.

14.      **(original)** The method of claim 13, further comprising forming source and drain regions at corresponding end portions of the semiconductor layer.

15.      **(original)** The method of claim 14, wherein said forming of the source and drain electrodes comprises:

depositing a second metal layer on the second insulating layer; and

patterning the second metal layer to form the source and drain electrodes.

16. **(original)** The method of claim 15, wherein said forming of the opening portion comprises using the remaining photoresist layer as a planarization layer.

17. **(original)** The method of claim 16, wherein said forming of the pixel electrode and the semiconductor layer comprises forming the pixel electrode after forming the semiconductor layer.

18. **(original)** The method of claim 16, wherein said forming of the pixel electrode and the semiconductor layer comprises forming the pixel electrode before forming the semiconductor layer.

19. **(original)** The method of claim 15, further comprising:  
forming a third insulating layer over the surface of the substrate before the forming of the photoresist layer; and  
removing the remaining photoresist layer after the forming of the opening portion using the photoresist layer as a mask.

20. **(original)** The method of claim 19, wherein the third insulating layer comprises one of an oxide layer, a nitride layer and an acryl layer.

21. **(original)** The method of claim 7, wherein said forming of the opening portion comprises using the remaining photoresist layer as a planarization layer.

22. **(original)** The method of claim 7, further comprising:  
forming a third insulating layer over the surface of the substrate before the forming of the photoresist layer; and  
removing the remaining photoresist layer after the forming of the opening portion using the photoresist layer as a mask.

23. (new) A method of manufacturing a flat panel display, comprising:  
forming a thin film transistor and a pixel electrode on a buffered substrate, the pixel electrode being covered by one or more insulating layers during the formation of the thin film transistor;  
etching an opening in the one or more layers to expose a portion of the pixel electrode;  
forming an electroluminescence (EL) layer on the pixel electrode and in the opening; and  
forming a cathode over the EL layer.
24. (new) The method of claim 7, further comprising:  
forming the opening portion in the first and second insulating layers to have an area size smaller than the pixel electrode so that the EL layer does not have a surface with a tangent to an edge portion of the pixel electrode.